

# EE 471: Transport Phenomena in Solid State Devices

## HW 4

Due: 2/27/18

*Please show all working (including equations you use to calculate your answers).*

*All numerical answers should include units*

*Calculate numerical answers to 3 sig. figs.*

1. A vertical silicon diode with a shallow P diffusion of  $N_a = 1.5 \times 10^{18} \text{ cm}^{-3}$  above a deep N diffusion of  $N_d = 1.1 \times 10^{16} \text{ cm}^{-3}$  is to be used as a photodiode.

Assume that:

$$\text{Electron minority carrier lifetime } \tau_n = 6 \times 10^{-7} \text{ s}$$

$$\text{Hole minority carrier lifetime } \tau_p = 1 \times 10^{-6} \text{ s}$$

$$\text{Electron mobility } \mu_n = 1150 \text{ cm}^2/\text{V}\cdot\text{s}$$

$$\text{Hole mobility } \mu_p = 180 \text{ cm}^2/\text{V}\cdot\text{s}$$

- If the bandgap of silicon is  $1.1 \text{ eV}$ , what can you say about the wavelength of light that might be absorbed by this photodiode? (3 points)
  - How should the diode normally be biased to act as a photodiode? Why? (3 points)
  - If the diode is reverse biased with  $V_r = 3.5\text{V}$ , what is the width of the depletion region? (3 points)
  - What are the minority carrier diffusion lengths in the N and P neutral regions? (6 points)
  - Estimate the transit time for a hole crossing the depletion region from the N-side to the P-side. (3 points)
  - The depth of the P diffusion is  $1 \mu\text{m}$  and the depth of the N diffusion is  $13 \mu\text{m}$ . Is this a short or a long photodiode as described in Lecture 6, Slide 15? What depth of silicon will be available to absorb photons and generate optical current? (4 points)
  - The photodiode is illuminated with light of  $\lambda = 700\text{nm}$ . At this wavelength, the absorption coefficient  $\alpha = 1000 \text{ cm}^{-1}$ . What fraction of the incident light will be absorbed in the active region of the photodiode? (4 points)
  - If the area of the photodiode is  $50\mu\text{m} \times 25\mu\text{m}$ , what power of incident light (in  $\text{W}/\text{cm}^2$ ) will be required to generate a photocurrent of  $5.0 \text{ nA}$ ? (4 points)
2. A new semiconductor has a direct bandgap of  $2.07 \text{ eV}$ . What would you expect to observe if a PN junction diode made with this material were forward biased? (5 points)